

COMPLETE SET OF PENDING CLAIMS

1. (Currently Amended) A method for cleaning semiconductor articles, comprising the steps of:

placing one ~~of~~ or more articles into a chamber;

rotating the articles within the chamber;

applying a heated liquid comprising water onto the rotating articles;

introducing ozone gas and carbon dioxide gas into the chamber, with the ozone oxidizing contaminants on the articles, to clean the articles.

2. (Original) The method of claim 1 wherein the liquid is heated to 50-200C.

3. (Original) The method of claim 1 wherein the liquid is heated to 75-150C.

4. (Original) The method of claim 1 wherein the liquid includes an acid.

5. (Original) The method of claim 1 further including the step of rinsing the articles.

6. (Original) The method of claim 5 further including the step of drying the articles.

7. (Original) The method of claim 6 further including the step of drying the articles using isopropyl alcohol.

8. (Currently Amended) The method of claim 1 wherein at least some of the ozone is entrained in the liquid, before the liquid is applied to the articles.

9. (Original) The method of claim 1 wherein the heated liquid is sprayed onto the articles.

10. (Original) The method of claim 1 wherein the articles comprise semiconductor material wafers.

11. (Original) The method of claim 1 wherein the liquid includes hydrogen peroxide.

12. (Currently Amended) A method for cleaning a wafer, comprising the steps of:

rotating the wafer;

applying a ~~heated~~ liquid comprising water onto the rotating wafer, with the liquid heated to 50-200C;

supplying ozone gas and carbon dioxide gas to the wafer, with the ozone oxidizing contaminants on the wafer, to clean the wafer.

13. (Cancelled)

14. (Currently Amended) The method of claim 12 wherein at least some of the ozone is entrained in the liquid, before the liquid is applied to the articles.

15. (Original) The method of claim 12 further including the step of placing the wafer into a chamber, and wherein the ozone gas is mixed with the carbon dioxide gas before the gases are supplied to the wafer in the chamber.

16. (Original) The method of claim 12 wherein the heated liquid is sprayed onto the rotating wafer.

17-20. (Cancelled).

21. (New) A method for cleaning semiconductor wafers, comprising the steps of:

placing the wafers into a chamber;

rotating the wafers;

applying a liquid including water heated to 50-200C generally uniformly
onto the wafers;

providing ozone gas and carbon dioxide gas into the chamber, with the
ozone oxidizing contaminants on the surface of the article.

22. (New) The method of claim 21 with the some of the ozone gas
entrained into the liquid, before the liquid is applied to the wafers.

23. (New) The method of claim 21 further including the step of applying
the liquid by spraying.